

ASR8N1200MEP05-X

1200V, 8mΩ, H-Bridge, Silicon Carbide MOSFET Module

Product Data Sheet

ASTC-3T03-226A A/0



爱仕特半导体

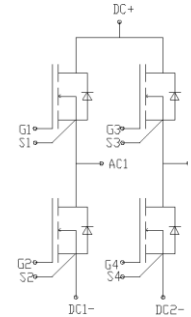
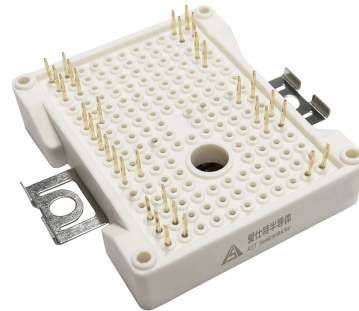
AST Semiconductor

General Description

The AST-MEP module incorporates AST's 1200V Gen3-X N-channel SiC MOSFET, solder pin type. NTC temperature sensor inside.

Features

- High Current Density
- Low Inductive Design
- Low Switching Losses
- Zero Turn-off Tail Current from MOSFET
- Normally-off, Fail-Safe Device Operation
- ZTA Internal Isolation



Applications

- High Frequency Switching Application
- DC/DC Converter
- Welding
- DC Charger for EV

Ordering Informations

Order Number	ASR8N1200MEP05-X
Marking	ASR8N1200MEP05
Package Type	MEP

Key Parameters

Symbol	Parameter	Values			Unit	Test Conditions
Absolute maximum rating						
V _{DS}	Drain-Source Voltage	1200			V	T _c =25°C
I _D	Drain Current (continuous)	200			A	T _c =25°C
T _J ; MAX	Junction Temperature	150			°C	
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics						
R _{DS(on)}	Static Drain-Source on Resistance	-	8.0	10.0	mΩ	V _{GS} =18V; I _D =200A; T _c =25°C
Dynamic characteristics						
Q _G	Total Gate Charge	-	412	-	nC	V _{DD} =800V; V _{GS} =-5/+18V; I _D =100A; T _c =25°C
Q _{GD}	Gate-Drain Charge	-	98	-		
Source-drain diode						
Q _{RR}	Reverse Recovery Charge	-	1226	-	nC	V _{GS} =-5/+18V; I _F =200A; V _R =800V; R _{GS(ext)} =50; Load=100μH; T _J =25°C

Absolute Maximum Ratings (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-Source Voltage	1200	V
V_{GS}	Gate-Source Voltage	-10/+22	V
I_D	Continuous DC Drain Current ($T_c=25^{\circ}\text{C}$)	200	A
	Continuous DC Drain Current ($T_c=85^{\circ}\text{C}$)	155	
I_{DM}	Drain Current (pulsed)	310	A
V_{isol}	Isolation Test Voltage ($f=50\text{Hz}$; $t=1\text{min}$)	3.0	kV
L_{Stray}	Stray Inductance	10	nH
T_J ; T_{stg}	Junction and Storage Temperature Range	-40 to +150	$^{\circ}\text{C}$
M_s	Mounting Force Per Clamp	40 - 80	N
$R_{th Jh}$	Thermal Resistance, Junction to Heatsink	0.15	$^{\circ}\text{C/W}$
M	Weight	39	g

MOSFET Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)						
BV_{DS}	Drain-Source Breakdown Voltage	1200	-	-	V	$V_{GS}=0\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current	-	-	20	μA	$V_{DS}=1200\text{V}$; $V_{GS}=0\text{V}$
I_{GSS}	Gate-Body Leakage Current	-	-	1.0	μA	$V_{GS}=-10/20\text{V}$; $V_{DS}=0\text{V}$
$V_{GS(th)}$	Gate Threshold Voltage	2	-	4	V	$V_{DS}=V_{GS}$; $I_D=20\text{mA}$
$R_{DS(on)}$	Static Drain-Source on Resistance	-	8.0	10.0	$\text{m}\Omega$	$V_{GS}=18\text{V}$; $I_D=200\text{A}$
$V_{GS(on)}$	Recommended Turn-on Voltage	-	18	-	V	Static
$V_{GS(off)}$	Recommended Turn-off Voltage	-	-5	-		
R_G	Gate Resistance	-	3.5	-	Ω	$V_{GS}=0\text{V}$; $f=1\text{MHz}$
Dynamic characteristics (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)						
C_{iss}	Input Capacitance	-	6.1	-	nF	$V_{DS}=1000\text{V}$; $f=100\text{KHz}$; $V_{AC}=25\text{mV}$
C_{oss}	Output Capacitance	-	192	-	pF	
C_{rss}	Reverse Transfer Capacitance	-	30	-	pF	
E_{on}	Turn-on Energy	-	5.0	-	mJ	$V_{DS}=800\text{V}$; $V_{GS}=-5/+18\text{V}$; $I_D=200\text{A}$; $R_{G(ext)}=5\Omega$; Load=100 μH
E_{off}	Turn-off Energy	-	7.5	-		
Q_{GS}	Gate-Source Charge	-	116	-	nC	$V_{DD}=800\text{V}$; $V_{GS}=-5/+18\text{V}$; $I_D=100\text{A}$
Q_{GD}	Gate-Drain Charge	-	98	-		
Q_G	Total Gate Charge	-	412	-		
$t_{d(on)}$	Turn-on Delay Time	-	54	-	ns	$V_{DS}=800\text{V}$; $V_{GS}=-5/+18\text{V}$; $I_D=200\text{A}$; $R_{G(ext)}=5\Omega$; Load=100 μH
t_r	Rise Time	-	65	-		
$t_{d(off)}$	Turn-off Delay Time	-	183	-		
t_f	Fall Time	-	34	-		

Body Diode Characteristics (at $T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
V_{FSD}	Forward Voltage	-	-	6	V	$V_{GS}=0\text{V}$; $I_F=100\text{A}$
I_S	Continuous Diode Forward Current	-	100	-	A	$V_{GS}=0\text{V}$; $T_C=25^{\circ}\text{C}$
t_{RR}	Reverse Recovery Time	-	113	-	ns	$V_{GS}=-5/+18\text{V}$; $I_F=200\text{A}$; $V_R=800\text{V}$; $R_{G(\text{ext})}=5\Omega$; Load=100 μH
Q_{RR}	Reverse Recovery Charge	-	1226	-	nC	
I_{RRM}	Peak Reverse Recovery Current	-	67	-	A	

NTC Thermistor Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
R_{25}	Rated Resistance	-	5.00	-	k Ω	$T_{NTC}=25^{\circ}\text{C}$
$\Delta R/R$	Deviation of R_{100}	-5	-	5	%	$T_{NTC}=100^{\circ}\text{C}$; $R_{100}=493.3\Omega$
$B_{25/50}$	Beta Value for 25°C to 50°C	-	3375	-	K	$R_2=R_{25}\exp [B_{25/50}(1/T_2-1/(298.15\text{K}))]$
$B_{25/80}$	Beta Value for 25°C to 80°C	-	3414	-	K	$R_2=R_{25}\exp [B_{25/80}(1/T_2-1/(298.15\text{K}))]$
$B_{25/100}$	Beta Value for 25°C to 100°C	-	3436	-	K	$R_2=R_{25}\exp [B_{25/100}(1/T_2-1/(298.15\text{K}))]$

Typical Performance

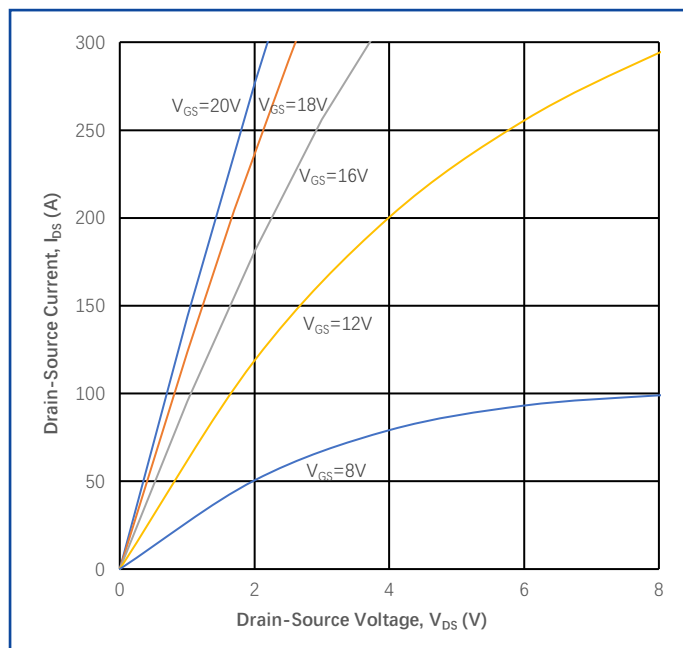


Figure 1
Output Characteristics ($T_J = 25^\circ\text{C}$)

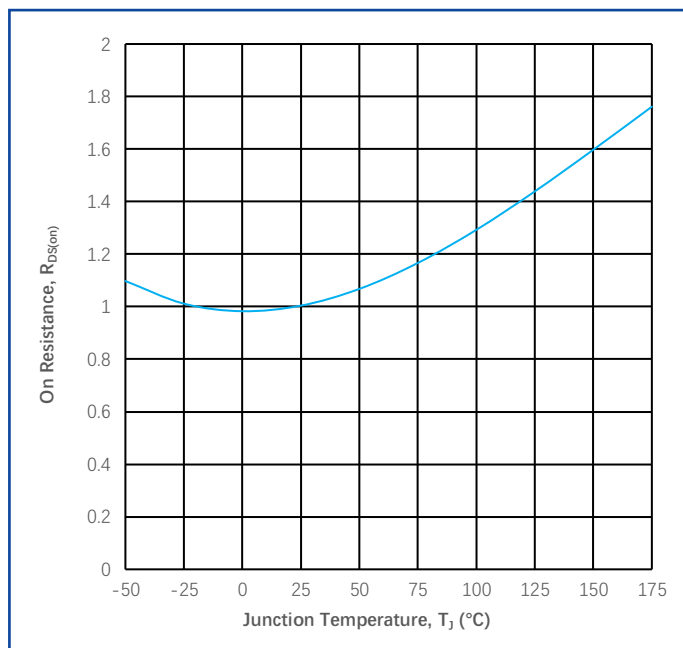


Figure 2
Normalized On-Resistance vs. Temperature

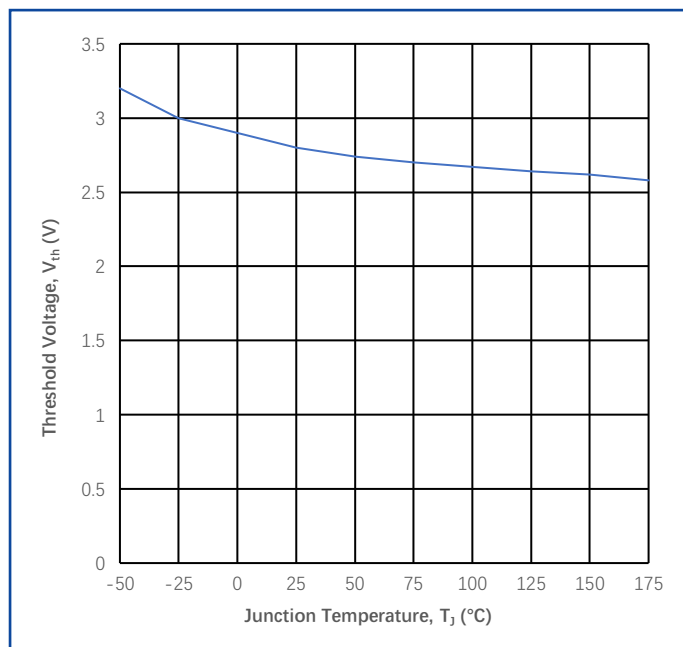


Figure 3
Threshold Voltage vs. Temperature

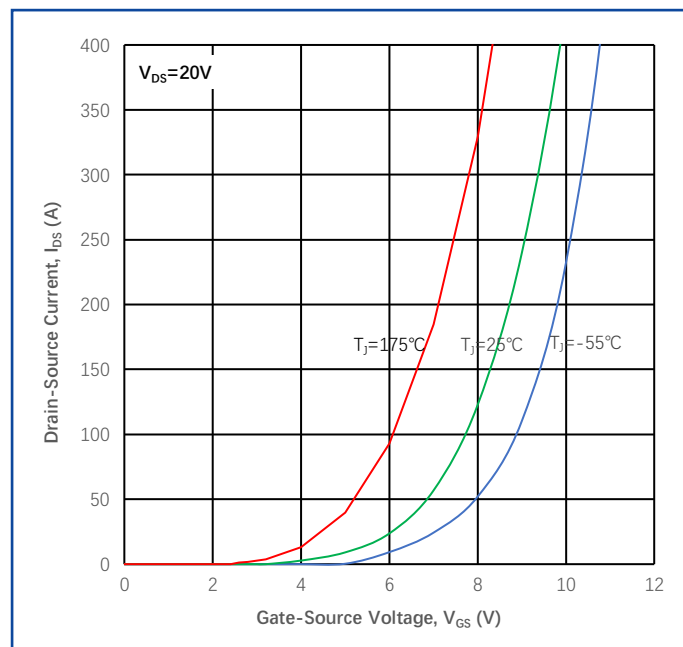


Figure 4
Transfer Characteristic for Various T_J

Typical Performance

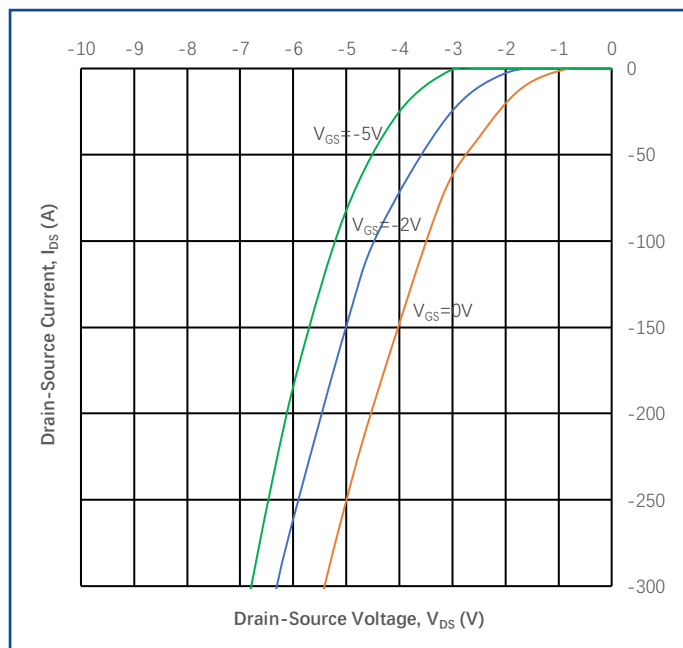


Figure 5
Diode Characteristic at 25°C

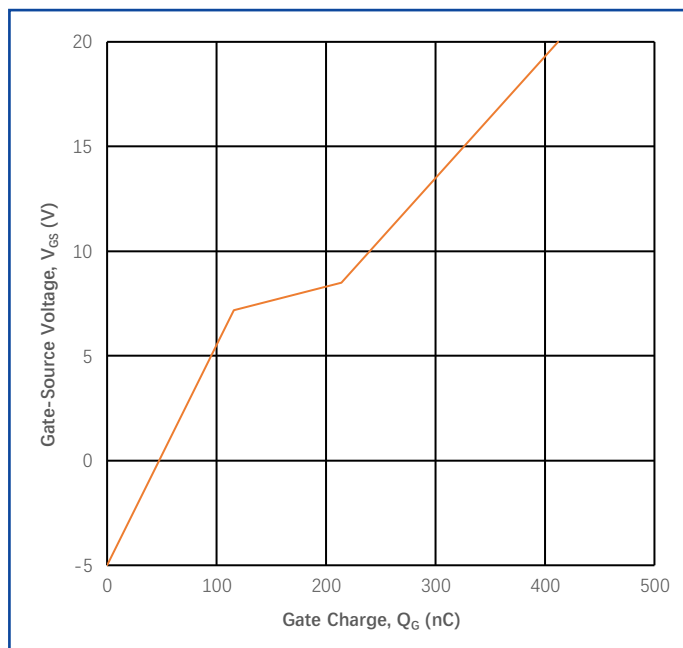


Figure 6
Typical Gate Charge Characteristics

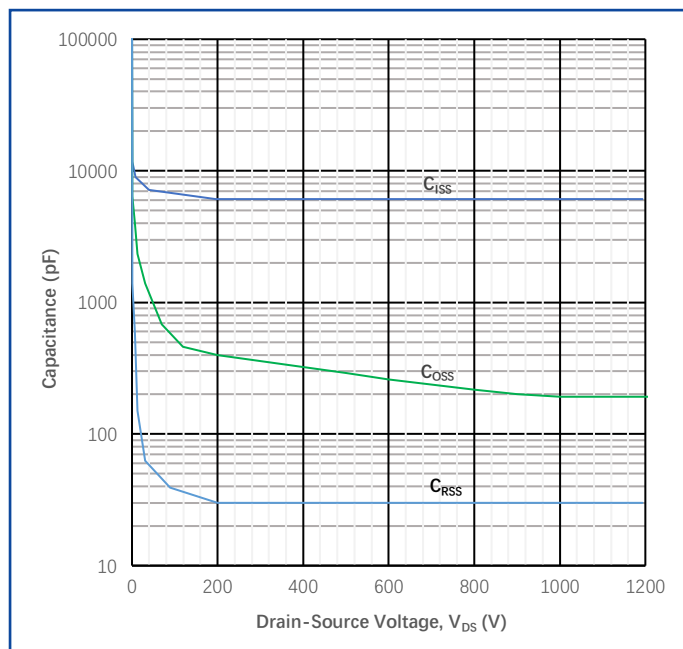


Figure 7
Typical Capacitances vs. Drain-Source Voltage

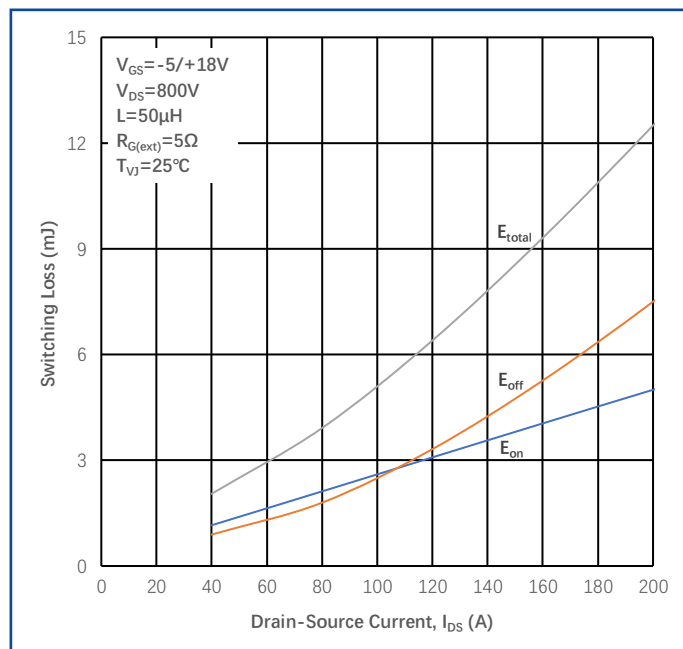


Figure 8
Inductive Switching Energy vs. Drain Current

Typical Performance

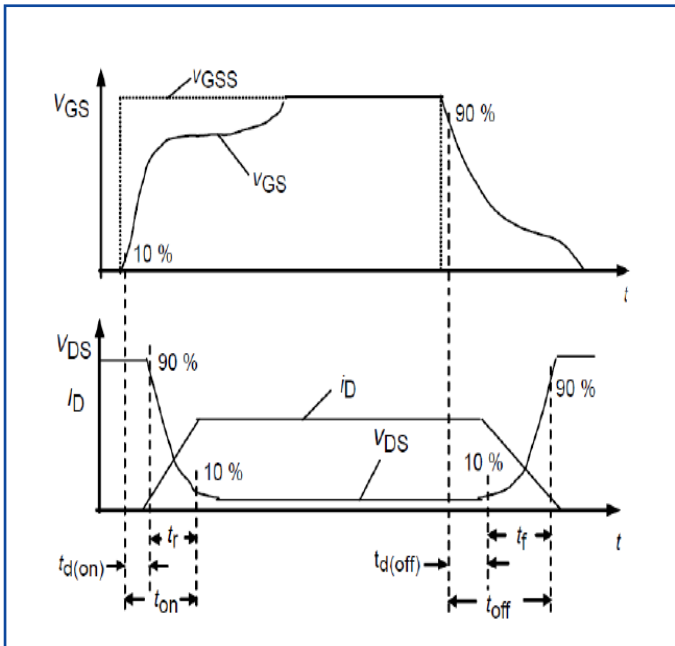


Figure 9
Switching Time Description

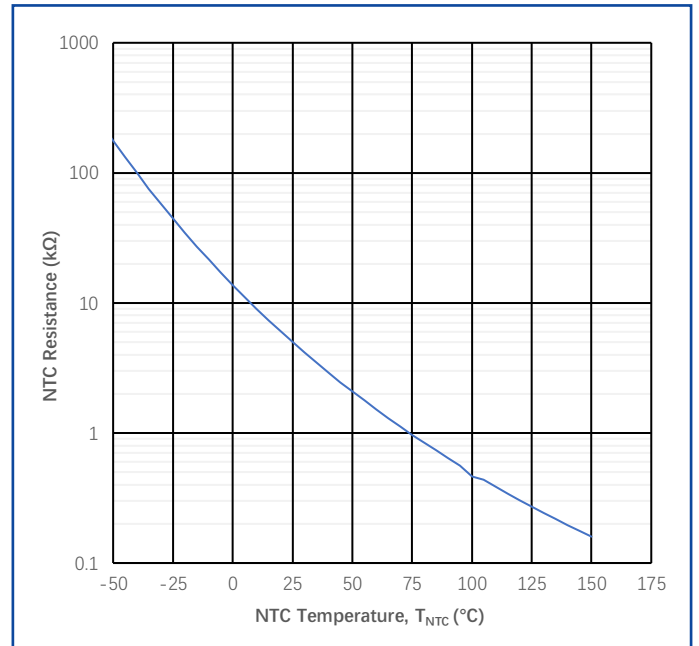
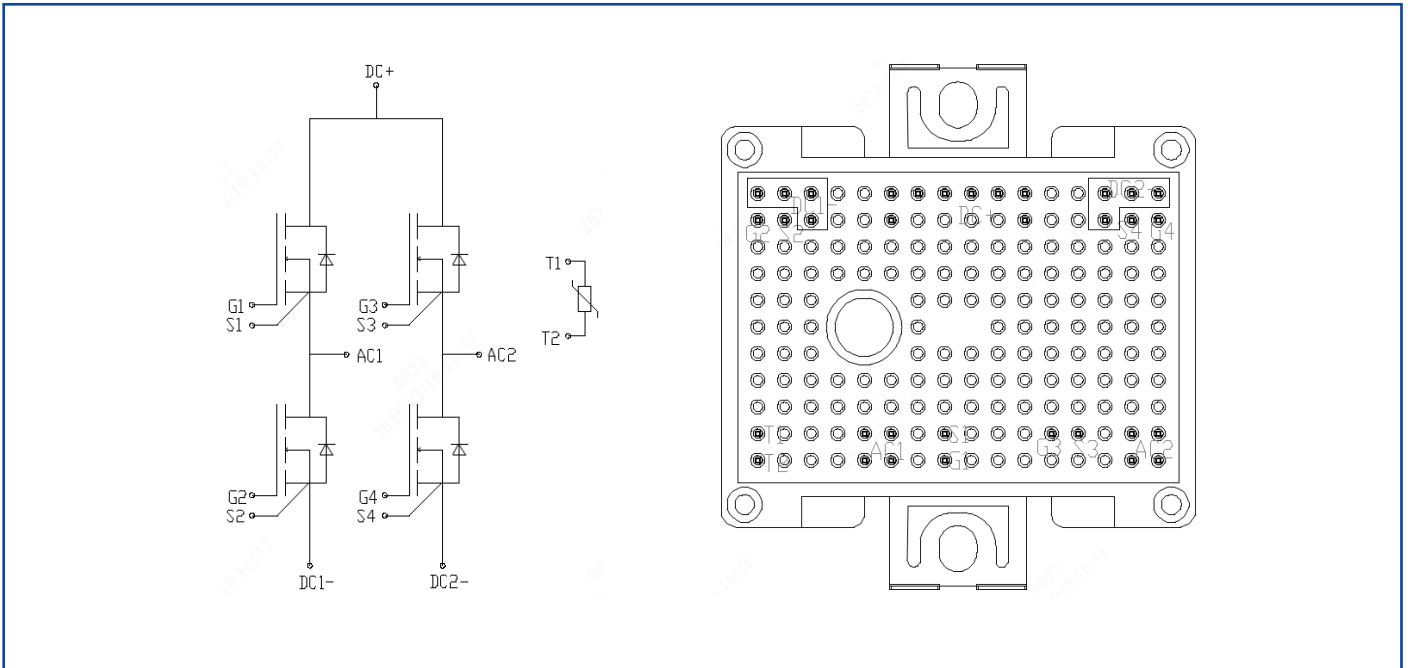


Figure 10
NTC-Temperature Characteristic (Typical)

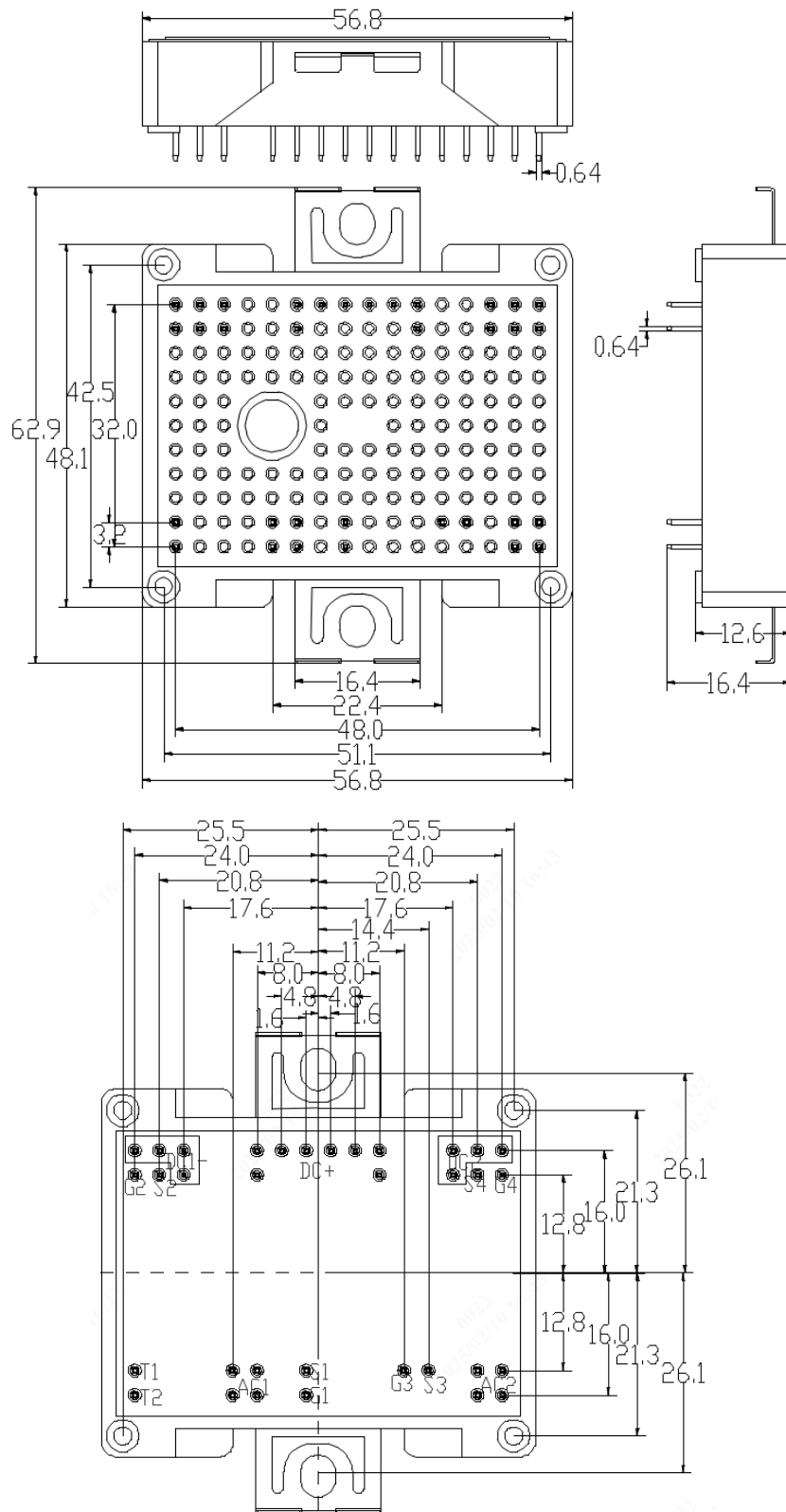
Circuit Diagram Headline





Package Dimensions(mm)

Package Type: MEP



未标注线性公差按 GB/1804-2000c 级执行	公差分段	0.5-3	3-6	6-30	30-120	120-400
	c 级	±0.2	±0.3	±0.5	±0.8	±1.2

Notes & Disclaimer

This document and the information contained herein are subject to change without notice. Any such change shall be evidenced by the publication of an updated version of this document by AST Semiconductor. No communication from any employee or agent of AST Semiconductor or any third party shall effect an amendment or modification of this document.

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, AST Semiconductor hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

Any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of AST Semiconductor in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

Except as otherwise explicitly approved by AST Semiconductor in a written document signed by authorized representatives, the products of AST Semiconductor may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

© 2026 Hangzhou AST Semiconductor Co., Ltd.
All Rights Reserved.

For more information, please visit: <http://www.astsic.com>